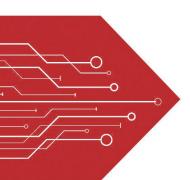
MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Brodnet data speet

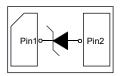
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DFN1610-2L



Circuit diagram

Marking H12N

Feature

- > 1600W Peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

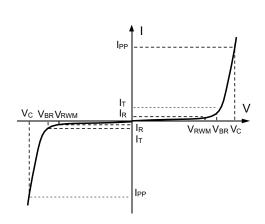
- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- ➤ Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- ➤ Qualified max reflow temperature:260°C
- ➤ Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil
- Device meets MSL3 requirements

Electronics Parameter

Symbol	Parameter	
V _{RWM}	Peak Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V_{BR}	Breakdown Voltage @ I _T	
lτ	Test Current	
I _{PP}	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
CJ	Junction Capacitance	









Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				12	V
Breakdown Voltage	V_{BR}	I _t =1mA	13.5	15.0		V
Reverse Leakage Current	I _R	V _{RWM} =12V			1	μA
Clamping Voltage	Vc	I _{PP} =65A t _P = 8/20μs		30.0	35.0	V
Junction Capacitance	C _j	V _R =0V f = 1MHz	300	355	400	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µS)	P _{pp}	1600	W
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Typical Characteristics

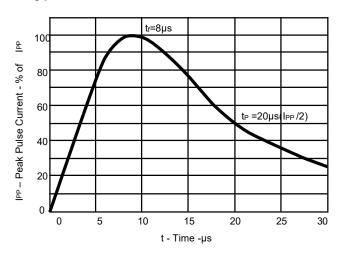


Fig 1.Pulse Waveform

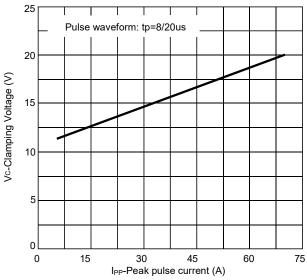


Fig 3. Clamping voltage vs. Peak pulse current

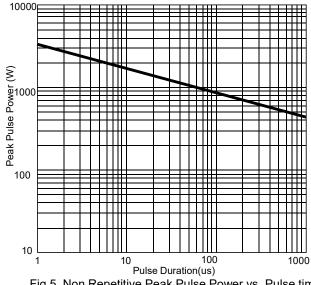


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

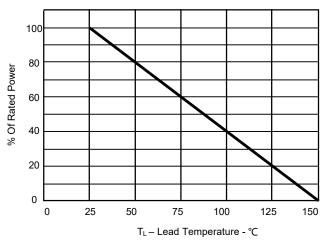


Fig 2.Power Derating Curve

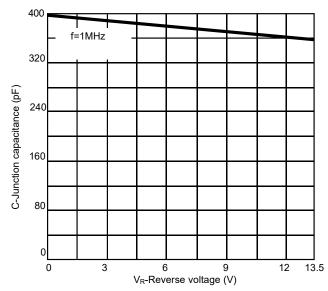
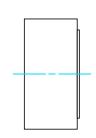


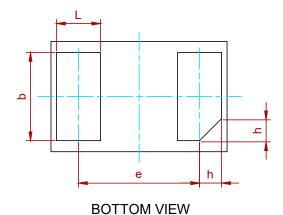
Fig 4. Capacitance vs. Reveres voltage



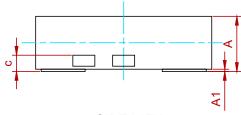
PACKAGE MECHANICAL DATA







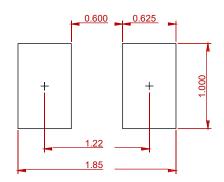
TOP VIEW



SIDE VIEW

Symbol	Di	Dimensions in Millimeters			
	Min.	Тур.	Max.		
A	0.45	0.50	0.55		
A1	0.00	0.02	0.05		
С		0.15 Ref.			
b	0.75	0.80	0.85		
L	0.35	0.40	0.45		
D	1.55	1.60	1.65		
E	0.95	1.00	1.05		
е		1.10 BSC			
h		0.20 Ref.			

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
PTVSHC2EN12VU-MS	DFN1610-2L	3000



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